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TITLE: MANUFACTURE OF SEMICONDUCTOR DEVICE AND METHOD FOR
FORMING INSULATING FILM
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INVENTOR-INFORMATION:

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ABSTRACT:

PROBLEM TO BE SOLVED: To prevent an organic insulating film from being oxidized, even when the organic insulating film is etched.

SOLUTION: On a semiconductor substrate 100, a first metallic wiring 101, a silicon nitride film 102, a first organic film 103 whose main component is an organic component, a silicon oxide film 104, a second organic film 105A which with its main component being an organic component, is patterned, and a mask pattern 108 comprising a titanium nitride film is formed, and then the silicon oxide film 104 is etched to form a patterned silicon oxide film 104A. Then a patterned second organic film 105A and the first organic film 103 are dry-etched using H2O plasma, respectively, so that a wiring groove 111 is formed on the patterned second organic film 105A, while a patterned first organic film 103A comprising a contact hole 110 is formed.

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